

INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION Generic Copy

27-JAN-2004

SUBJECT: ON Semiconductor Initial Product/Process Change Notification #13298

TITLE: Initial Notification for Transfer of Analog Bipolar Integrated Circuits Die Manufacturing

EFFECTIVE DATE: 27-May-2004

AFFECTED CHANGE CATEGORY: ON Semiconductor Fab Site

AFFECTED PRODUCT DIVISION: Analog Products

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact Sales Representative or Patrick Rousset <TTT252@onsemi.com>

NOTIFICATION TYPE:

Initial Product/Process Change Notification (IPCN)

First change notification sent to customers. IPCNs are issued at least 120 days prior to implementation of the change. An IPCN is advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan.

The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN).

This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 60 days prior to implementation of the change.

DESCRIPTION AND PURPOSE:

The purpose of this Initial PCN is to notify customers of ON Semiconductor's plan to qualify and transfer, production of the 17 Volt, 30 Volt, and 40 Volt Analog Bipolar integrated circuits from the ON Semiconductor East Greenwich facility in Rhode Island (USA) to the Tesla wafer fab located in Roznov, Czech Republic, over the next 12 months.

The 14 Volt and 50 Volt technologies have previously transferred from the ON Semiconductor East Greenwich facility in Rhode Island (USA)to the Tesla wafer fab located in Roznov, Czech Republic. (Refer to FPCN # 12511 and FPCN# 12512).

An additional IPCN may be issued at a later date for additional devices impacted by the closure of the East Greenwich facility. The integrated circuits design, electrical specifications, and mask sets will remain identical. A full electrical characterization over the temperature range will be performed for each product to ensure device functionality and electrical specifications.

Qualification tests are designed to show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards. ON Semiconductor recommends that customers evaluate sample units in each associated application circuit to ensure there are no unexpected electrical incompatibilities.

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Multiple final PCNs will be published, starting in the third quarter of 2004, providing the qualification results and effective planned production release dates at Tesla for specific devices.

QUALIFICATION PLAN:

Qualification of each device type to be transferred is being performed to the following requirements:

- 1) Three temperature electrical characterization (2 to 3 lots, 50 units each lot)
- 2) ESD testing (1 lot), Human Body Model and Machine Model
- 3) Latch up testing (1 lot)

Reliability testing will be performed on qualification vehicles chosen based on die size, complexity and run rates. The number of qualification vehicles being used to qualify each process is based upon the number of part types actually running on the process.

Analog integrated circuits processed with the 17 Volt technology

3 Lots HTOL, ELFR, PC, THB CS45008D14

CS9002LFT48 3 Lots HTOL, PC, AC, TC

CS42046D8 3 Lots HTOL CS42076D8 3 Lots HTOL

Analog integrated circuits processed with the 30 Volt technology

CS61012DW28 3 Lots HTOL, ELFR, PC, THB, AC, TC

CS51411D8 3 Lots HTOL, ELFR, PC, TC

CS8190N16 3 Lots HTOL CS41115D8 3 Lots HTOL CS44116T7 3 Lots HTOL

Analog integrated circuits processed with the 40 Volt technology

CS68059DW24 3 Lots HTOL, ELFR, PC, THB, AC, TC

3 Lots HTOL CS68004DW16

Planned reliability tests are:

Test Early Life (ELFR)	Conditions Ta=+125DegC, Bias	Duration 48 hrs
High Temp.Operating Life (HTOL)	Ta=+125DegC, Bias	1008 hrs
Temp. Cycle (TC)*	-65DegC to +150DegC	500 cycle

Autoclave (AC) * +121DegC/15psig/100%RH 96 hrs

Temp. Humidity bias (THB)* +85DegC /85%RH 1008 hrs

Wire Bond Pull Strength (BPS)* After TC, 30 bonds/5 units

Wire Bond Shear Strength (BS) 30 bonds/5 units

*Note: These tests may be performed with preconditionned parts depending upon the device type used.

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AFFECTED DEVICE LIST (WITHOUT SPECIALS):

PART

CS1124YD8

CS1124YDR8

CS2841BEBN8

CS2841BED14

CS2841BEDR14

CS3341YD14

CS3341YDR14

CS3351YD14

CS3351YDR14

CS4121EDWF20

CS4121EDWFR20

CS4121ENF16

CS5112YDWF24

CS5112YDWFR24

CS51411ED8

CS51411EDR8

CS51411GD8

CS51411GDR8

CS51412ED8

CS51412EDR8

CS51412GD8

CS51412GDR8

CS51413ED8

CS51413EDR8

CS51413GD8

CS51413GDR8

CS51414ED8

CS51414EDR8

CS51414GD8

CS51414GDR8

CS5171ED8

CS5171EDR8

CS5171GD8

CS5171GDR8

CS5172ED8 CS5172EDR8

CS5172GD8

CS5172GDR8

CS5173ED8

CS5173EDR8 CS5173GD8

CS5173GDR8

CS5174ED8

CS5174EDR8

CS5174GD8

CS5174GDR8

CS8120YD14

CS8120YDP5

CS8120YDPR5

CS8120YDR14 CS8120YN8

CS8120YT5

CS8120YTHA5

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CS8120YTVA5

CS8122YT5

CS8122YTHA5

CS8122YTVA5

CS8126-1YDPS7

CS8126-1YDPSR7

CS8126-1YDPSR7G

CS8126-1YT5

CS8126-1YTHA5

CS8126-1YTHE5

CS8126-1YTHER5

CS8126-1YTVA5

CS8129YDW16

CS8129YDWR16

CS8129YT5

CS8129YTHA5

CS8129YTVA5

CS8156YT5

CS8156YTHA5

CS8156YTVA5

CS8182YDF8

CS8182YDFR8

CS8182YDPS5

CS8182YDPSR5

CS8183YDWF20

CS8183YDWFR20

CS8190EDWF20

CS8190EDWFR20

CS8190ENF16

CS8321YDP3

CS8321YDPR3

CS8321YT3

CS8371ET7

CS8371ETVA7

NCP5173MN

NCP5173MNR2

NCP5331FTR2

NCP5422ADR2

NCP5425DB

NCP5425DBR2

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